

Notice of References CitedApplication/Control No.
09/754,926Applicant(s)/Patent Under
Reexamination
AHN ET AL.Examiner
Erik KielinArt Unit
2813

Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,923,056	07-1999	Lee et al.	257/192
	B	US-5,856,017	01-1999	Matsuda et al.	428/446
	C	US-6,280,810 B1	08-2001	Nakamura et al.	369/283
	D	US-6,300,202 B1	10-2001	Hobbs et al.	438/287
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	JP 60167352 A	08-1985	Japan	FUJISADA, HIROYUKI	H01L 21/86
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Vossen and Kern, Thin Film Processes II, Academic Press: Boston, 1991, pp. 80-81, 108-109, 113-115, 188, 200.
	V	Wolf, Silicon Processing for the VLSI Era, Vol. 1 : Process Technology, Lattice Press: Sunset Beach, CA 1986, p. 5.
	W	Manchanda et al. "Gate quality doped high K films for CMOS beyond 100 nm: 3-10 nm Al ₂ O ₃ with low leakage and low interface states," IEDM 1998, 6-9 December 1998, pp. 605-608.
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.